

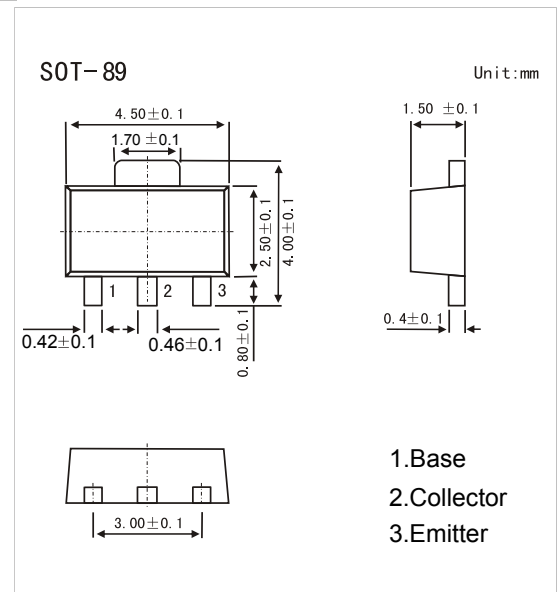
## SOT-89 Plastic-Encapsulate Transistors

### Features

- Small Flat Package
- High Transition Frequency
- High Voltage
- Complementary to 2SA1201
- NPN Transistors

### MECHANICAL DATA

- Case style: SOT-89 molded plastic
- Mounting position: any



## MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CB0}$	120	V
Collector - Emitter Voltage	$V_{CE0}$	120	
Emitter - Base Voltage	$V_{EB0}$	5	
Collector Current - Continuous	$I_C$	800	mA
Base Current	$I_B$	160	
Collector Power Dissipation	$P_C$	500	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	250	°C/W
Junction Temperature	$T_J$	150	°C
Storage Temperature Range	$T_{stg}$	-55 to 150	

### PACKAGE INFORMATION

Device	Package	Shipping
2SC2881	SOT-89	1000/Tape&Reel

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CB0}$	$I_C = 100\mu A, I_E = 0$	120			V
Collector- emitter breakdown voltage	$V_{CE0}$	$I_C = 10mA, I_B = 0$	120			
Emitter - base breakdown voltage	$V_{EB0}$	$I_E = 100\mu A, I_C = 0$	5			
Collector-base cut-off current	$I_{CBO}$	$V_{CB} = 120V, I_E = 0$			0.1	uA
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 5V, I_C = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500mA, I_B = 50mA$			1	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500mA, I_B = 50mA$			1.2	
Base - emitter voltage	$V_{BE}$	$V_{CE} = 5V, I_C = 0.5A$			1	
DC current gain	$h_{FE}$	$V_{CE} = 5V, I_C = 100mA$	80		240	
Collector output capacitance	$C_{ob}$	$V_{CB} = 10V, I_E = 0, f = 1MHz$			30	pF
Transition frequency	$f_T$	$V_{CE} = 5V, I_C = 100mA$		120		MHz

### Classification of $h_{FE}$

Type	2SC2881-O	2SC2881-Y
Range	80-160	120-240
Marking	CO*	CY*

# RATINGS AND CHARACTERISTIC CURVES

## Typical Characteristics

